Low-power dual function gate Rev. 6 — 21 October 2010

Product data sheet

General description 1.

The 74AUP1G885 provides two functions in one device. The output state of the outputs (1Y, 2Y) is determined by the inputs (A, B and C). The output 1Y provides the Boolean function: $1Y = A \times C$. The output 2Y provides the Boolean function: $2Y = A \times B + A \times C$.

Schmitt-trigger action at all inputs makes the circuit tolerant to slower input rise and fall times across the entire V_{CC} range from 0.8 V to 3.6 V.

This device ensures a very low static and dynamic power consumption across the entire V_{CC} range from 0.8 V to 3.6 V.

This device is fully specified for partial power-down applications using IOFF. The IOFF circuitry disables the output, preventing a damaging backflow current through the device when it is powered down.

2. **Features and benefits**

- Wide supply voltage range from 0.8 V to 3.6 V
- High noise immunity
- Complies with JEDEC standards:
 - JESD8-12 (0.8 V to 1.3 V)
 - JESD8-11 (0.9 V to 1.65 V)
 - JESD8-7 (1.2 V to 1.95 V)
 - JESD8-5 (1.8 V to 2.7 V)
 - JESD8-B (2.7 V to 3.6 V)
- ESD protection:
 - HBM JESD22-A114F Class 3A exceeds 5000 V
 - MM JESD22-A115-A exceeds 200 V
 - CDM JESD22-C101E exceeds 1000 V
- Low static power consumption; $I_{CC} = 0.9 \mu A$ (maximum)
- Latch-up performance exceeds 100 mA per JESD78 Class II
- Inputs accept voltages up to 3.6 V
- Low noise overshoot and undershoot < 10 % of V_{CC}
- I_{OFF} circuitry provides partial Power-down mode operation
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C



3. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74AUP1G885DC	–40 °C to +125 °C	VSSOP8	plastic very thin shrink small outline package; 8 leads; body width 2.3 mm	SOT765-1
74AUP1G885GT	–40 °C to +125 °C	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body 1 \times 1.95 \times 0.5 mm	SOT833-1
74AUP1G885GF	–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body $1.35 \times 1 \times 0.5$ mm	SOT1089
74AUP1G885GD	–40 °C to +125 °C	XSON8U	plastic extremely thin small outline package; no leads; 8 terminals; UTLP based; body $3 \times 2 \times 0.5$ mm	SOT996-2
74AUP1G885GM	–40 °C to +125 °C	XQFN8U	plastic extremely thin quad flat package; no leads; 8 terminals; UTLP based; body $1.6 \times 1.6 \times 0.5$ mm	SOT902-1
74AUP1G885GN	–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body $1.2 \times 1.0 \times 0.35$ mm	SOT1116
74AUP1G885GS	–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body $1.35 \times 1.0 \times 0.35$ mm	SOT1203

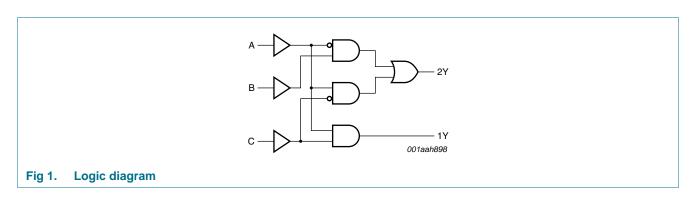
4. Marking

Table 2.Marking codes

5	
Type number	Marking code ^[1]
74AUP1G885DC	pS8
74AUP1G885GT	pS8
74AUP1G885GF	58
74AUP1G885GD	pS8
74AUP1G885GM	pS8
74AUP1G885GN	58
74AUP1G885GS	58

[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

5. Functional diagram

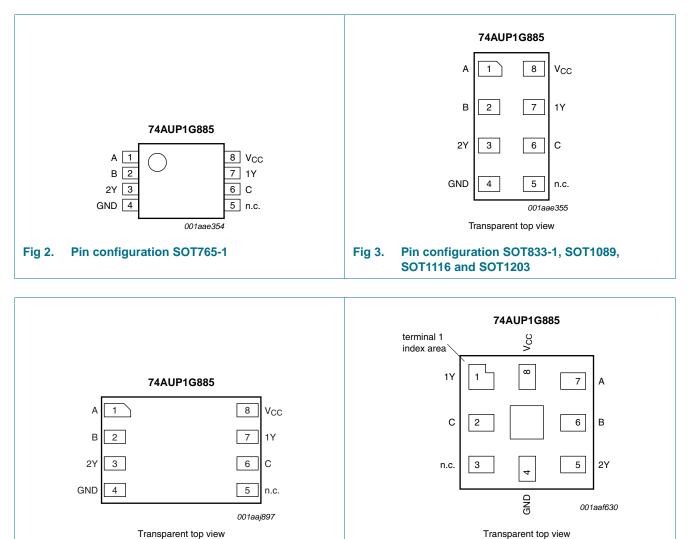


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Pinning information 6.

6.1 Pinning



Transparent top view

Fig 5. Pin configuration SOT902-1

6.2 Pin description

Pin configuration SOT996-2

Discute a substitution

Symbol	Pin		Description	
	SOT765-1, SOT833-1, SOT1089, SOT996-2, SOT1116 and SOT1203	SOT902-1		
A, B, C	1, 2, 6	7, 6, 2	data input	
GND	4	4	ground (0 V)	
n.c.	5	3	not connected	
1Y, 2Y	7, 3	1, 5	data output	
V _{CC}	8	8	supply voltage	
74AUP1G885	All information provide	d in this document is subject t	to legal disclaimers	© NXP B.V. 2010. All rights reserved.

Fig 4.

7. Functional description

Table 4.	Function table ^[1]					
Input			Output			
Α	В	C	1Y	2Y		
L	L	L	L	L		
Н	L	L	L	Н		
L	Н	L	L	Н		
Н	Н	L	L	Н		
L	L	Н	L	L		
Н	L	Н	Н	L		
L	Н	Н	L	Н		
Н	Н	Н	Н	L		

[1] H = HIGH voltage level; L = LOW voltage level.

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+4.6	V
I _{IK}	input clamping current	V _I < 0 V	-50	-	mA
VI	input voltage		<u>[1]</u> –0.5	+4.6	V
I _{OK}	output clamping current	V _O < 0 V	-50	-	mA
Vo	output voltage	Active mode and Power-down mode	<u>[1]</u> –0.5	+4.6	V
lo	output current	$V_{O} = 0 V$ to V_{CC}	-	±20	mA
I _{CC}	supply current		-	50	mA
I _{GND}	ground current		-50	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 \ ^{\circ}C \ to \ +125 \ ^{\circ}C$	[2] _	250	mW

[1] The minimum input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For VSSOP8 packages: above 110 °C the value of P_{tot} derates linearly with 8.0 mW/K.

For XSON8, XSON8U and XQFN8U packages: above 118 °C the value of Ptot derates linearly with 7.8 mW/K.

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9. Recommended operating conditions

Table 6.	Operating conditions				
Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		0.8	3.6	V
VI	input voltage		0	3.6	V
Vo	output voltage	Active mode	0	V _{CC}	V
		Power-down mode; $V_{CC} = 0 V$	0	3.6	V
T _{amb}	ambient temperature		-40	+125	°C
$\Delta t / \Delta V$	input transition rise and fall rate	$V_{CC} = 0.8 V \text{ to } 3.6 V$	-	200	ns/V

10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T _{amb} = 2	5 °C					
V _{IH}	HIGH-level input voltage	$V_{CC} = 0.8 V$	$0.70\times V_{CC}$	-	-	V
		$V_{CC} = 0.9 \text{ V}$ to 1.95 V	$0.65 \times V_{CC}$	-	-	V
		V_{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		V_{CC} = 3.0 V to 3.6 V	2.0	-	-	V
V _{IL}	LOW-level input voltage	$V_{CC} = 0.8 V$	-	-	$0.30\times V_{CC}$	V
		$V_{CC} = 0.9 V$ to 1.95 V	-	-	$0.35 \times V_{CC}$	V
		V_{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	-	-	0.9	V
V _{OH}	HIGH-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		I_{O} = –20 $\mu\text{A};V_{CC}$ = 0.8 V to 3.6 V	$V_{CC}-0.1$	-	-	V
		$I_{O} = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.75\times V_{CC}$	-	-	V
		$I_{O} = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	1.11	-	-	V
		I_{O} = -1.9 mA; V_{CC} = 1.65 V	1.32	-	-	V
		$I_{O} = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	2.05	-	-	V
		$I_{O} = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.9	-	-	V
		$I_{O} = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.72	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.6	-	-	V

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{OL}	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		I_{O} = 20 $\mu A;$ V_{CC} = 0.8 V to 3.6 V	-	-	0.1	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	$0.3\times V_{CC}$	V
		$I_0 = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	-	-	0.31	V
		I_{O} = 1.9 mA; V_{CC} = 1.65 V	-	-	0.31	V
		I_0 = 2.3 mA; V_{CC} = 2.3 V	-	-	0.31	V
		$I_0 = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.44	V
		$I_0 = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.31	V
		$I_0 = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.44	V
I _I	input leakage current	$V_I = GND$ to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	±0.1	μA
I _{OFF}	power-off leakage current	V_{I} or V_{O} = 0 V to 3.6 V; V_{CC} = 0 V	-	-	±0.2	μΑ
ΔI_{OFF}	additional power-off leakage current	$V_1 \text{ or } V_0 = 0 \text{ V to } 3.6 \text{ V};$ $V_{CC} = 0 \text{ V to } 0.2 \text{ V}$	-	-	±0.2	μΑ
I _{CC}	supply current	$\label{eq:VI} \begin{array}{l} V_{I} = GND \text{ or } V_{CC}; I_{O} = 0 \; A; \\ V_{CC} = 0.8 \; V \; to \; 3.6 \; V \end{array}$	-	-	0.5	μΑ
ΔI_{CC}	additional supply current		<u>[1]</u> -	-	40	μΑ
CI	input capacitance	V_{CC} = 0 V to 3.6 V; V_{I} = GND or V_{CC}	-	0.6	-	pF
Co	output capacitance	$V_{O} = GND; V_{CC} = 0 V$	-	1.3	-	pF
T _{amb} = -	40 °C to +85 °C					
VIH	HIGH-level input voltage	$V_{CC} = 0.8 V$	$0.70\times V_{CC}$	-	-	V
		$V_{CC} = 0.9 \text{ V} \text{ to } 1.95 \text{ V}$	$0.65 \times V_{CC}$	-	-	V
		V_{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	2.0	-	-	V
V _{IL}	LOW-level input voltage	$V_{CC} = 0.8 V$	-	-	$0.30\times V_{CC}$	V
		$V_{CC} = 0.9 \text{ V} \text{ to } 1.95 \text{ V}$	-	-	$0.35 \times V_{CC}$	V
		V_{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	-	-	0.9	V
V _{ОН}	HIGH-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		I_{O} = -20 μ A; V_{CC} = 0.8 V to 3.6 V	$V_{CC}-0.1$	-	-	V
		$I_0 = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.7 imes V_{CC}$	-	-	V
		$I_{O} = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	1.03	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.30	-	-	V
		$I_{O} = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.97	-	-	V
		$I_{O} = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.85	-	-	V
		$I_0 = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.67	-	-	V
		$I_0 = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.55	_	_	V

Table 7. Static characteristics ... continued

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{OL}	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		I_{O} = 20 μ A; V_{CC} = 0.8 V to 3.6 V	-	-	0.1	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	$0.3 \times V_{CC}$	V
		I _O = 1.7 mA; V _{CC} = 1.4 V	-	-	0.37	V
		I _O = 1.9 mA; V _{CC} = 1.65 V	-	-	0.35	V
		I_{O} = 2.3 mA; V_{CC} = 2.3 V	-	-	0.33	V
		I_{O} = 3.1 mA; V_{CC} = 2.3 V	-	-	0.45	V
		I_{O} = 2.7 mA; V_{CC} = 3.0 V	-	-	0.33	V
		I_{O} = 4.0 mA; V_{CC} = 3.0 V	-	-	0.45	V
I _I	input leakage current	$V_{\rm I}$ = GND to 3.6 V; $V_{\rm CC}$ = 0 V to 3.6 V	-	-	±0.5	μΑ
I _{OFF}	power-off leakage current	V_{I} or V_{O} = 0 V to 3.6 V; V_{CC} = 0 V	-	-	±0.5	μΑ
ΔI_{OFF}	additional power-off leakage current	$V_1 \text{ or } V_0 = 0 \text{ V to } 3.6 \text{ V};$ $V_{CC} = 0 \text{ V to } 0.2 \text{ V}$	-	-	±0.6	μA
I _{CC}	supply current	$\label{eq:VI} \begin{array}{l} V_{I} = GND \text{ or } V_{CC}; \ I_{O} = 0 \ A; \\ V_{CC} = 0.8 \ V \ \text{to} \ 3.6 \ V \end{array}$	-	-	0.9	μA
∆l _{CC}	additional supply current		<u>[1]</u> -	-	50	μA
T _{amb} = -4	40 °C to +125 °C					
	HIGH-level input voltage	$V_{CC} = 0.8 V$	$0.75 imes V_{CC}$; -	-	V
		$V_{CC} = 0.9 V \text{ to } 1.95 V$	$0.70 imes V_{CC}$; -	-	V
		V_{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		$V_{CC} = 3.0 V \text{ to } 3.6 V$	2.0	-	-	V
V _{IL}	LOW-level input voltage	$V_{CC} = 0.8 V$	-	-	$0.25\times V_{CC}$	V
		$V_{CC} = 0.9 V \text{ to } 1.95 V$	-	-	$0.30\times V_{CC}$	V
		V_{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		$V_{CC} = 3.0 V \text{ to } 3.6 V$	-	-	0.9	V
V _{он}	HIGH-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		I_O = –20 $\mu\text{A};~V_{CC}$ = 0.8 V to 3.6 V	$V_{CC} - 0.11$	-	-	V
		$I_{O} = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.6\times V_{CC}$	-	-	V
		$I_{O} = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	0.93	-	-	V
		I_{O} = -1.9 mA; V_{CC} = 1.65 V	1.17	-	-	V
		I_{O} = -2.3 mA; V_{CC} = 2.3 V	1.77	-	-	V
		$I_{O} = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.67	-	-	V
		I_{O} = -2.7 mA; V_{CC} = 3.0 V	2.40	-	-	V
		I_{O} = -4.0 mA; V_{CC} = 3.0 V	2.30	-	-	V

Static characteristics ... continued Table 7.

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{OL}	LOW-level output voltage	$V_I = V_{IH} \text{ or } V_{IL}$				
		I_{O} = 20 $\mu A;$ V_{CC} = 0.8 V to 3.6 V	-	-	0.11	V
		$I_{O} = 1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	-	-	$0.33 \times V_{CC}$	V
		$I_0 = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	-	-	0.41	V
		I_{O} = 1.9 mA; V_{CC} = 1.65 V	-	-	0.39	V
		$I_0 = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.36	V
		$I_{O} = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.50	V
		I_{O} = 2.7 mA; V_{CC} = 3.0 V	-	-	0.36	V
		I_{O} = 4.0 mA; V_{CC} = 3.0 V	-	-	0.50	V
I _I	input leakage current	$V_{\rm I}$ = GND to 3.6 V; $V_{\rm CC}$ = 0 V to 3.6 V	-	-	±0.75	μΑ
I _{OFF}	power-off leakage current	V_{I} or V_{O} = 0 V to 3.6 V; V_{CC} = 0 V	-	-	±0.75	μΑ
ΔI_{OFF}	additional power-off leakage current	V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	±0.75	μΑ
I _{CC}	supply current	$\label{eq:VI} \begin{array}{l} V_{I} = GND \text{ or } V_{CC}; \ I_{O} = 0 \ A; \\ V_{CC} = 0.8 \ V \ \text{to} \ 3.6 \ V \end{array}$	-	-	1.4	μΑ
ΔI_{CC}	additional supply current	$V_{I} = V_{CC} - 0.6 \text{ V}; I_{O} = 0 \text{ A};$ $V_{CC} = 3.3 \text{ V}$	<u>[1]</u> _	-	75	μΑ

Table 7. Static characteristics ...continued

[1] One input at V_{CC} – 0.6 V, other inputs at V_{CC} or GND.

11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V; for test circuit see Figure 7.

Symbo	Parameter	Conditions		25 °C		-40	0 °C to +1	25 °C	Unit
			Min	Typ[1]	Мах	Min	Max (85 °C)	Max (125 °C)	
C _L = 5	pF						1		
t _{pd}	propagation delay	A, C to 1Y; see Figure 6							
		$V_{CC} = 0.8 V$	-	17.3	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V} \text{ to } 1.3 \text{ V}$	1.1	5.2	9.7	0.9	12.8	14.2	ns
		$V_{CC} = 1.4 \text{ V} \text{ to } 1.6 \text{ V}$	1.2	3.7	5.9	1.0	7.8	8.6	ns
		V_{CC} = 1.65 V to 1.95 V	1.1	3.0	4.8	0.9	6.2	6.9	ns
		V_{CC} = 2.3 V to 2.7 V	1.1	2.4	3.6	1.0	4.1	4.5	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	1.1	2.1	3.1	1.0	3.6	4.1	ns
		A, B to 2Y; see Figure 6							
		$V_{CC} = 0.8 V$	-	21.5	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V} \text{ to } 1.3 \text{ V}$	1.7	6.0	12.7	1.4	12.8	14.2	ns
		$V_{CC} = 1.4 \text{ V} \text{ to } 1.6 \text{ V}$	1.7	4.2	7.2	1.4	7.8	8.7	ns
		$V_{CC} = 1.65 \text{ V} \text{ to } 1.95 \text{ V}$	1.4	3.3	5.8	1.2	6.5	7.2	ns
		V_{CC} = 2.3 V to 2.7 V	1.2	2.6	4.1	1.0	4.7	5.2	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	1.1	2.3	3.5	0.9	3.8	4.2	ns
C _L = 10) pF								
t _{pd}	propagation delay	A, C to 1Y; see Figure 6							
		$V_{CC} = 0.8 V$	-	20.8	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V} \text{ to } 1.3 \text{ V}$	1.2	6.1	11.4	1.2	14.6	16.1	ns
		$V_{CC} = 1.4 \text{ V} \text{ to } 1.6 \text{ V}$	1.4	4.3	7.2	1.2	8.7	9.6	ns
		V_{CC} = 1.65 V to 1.95 V	1.4	3.6	5.7	1.3	6.8	7.5	ns
		V_{CC} = 2.3 V to 2.7 V	1.4	2.9	4.2	1.2	4.8	5.4	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	1.4	2.7	3.9	1.3	4.1	4.6	ns
		A, B to 2Y; see Figure 6							
		$V_{CC} = 0.8 V$	-	25.0	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V} \text{ to } 1.3 \text{ V}$	1.8	6.9	14.4	1.7	14.6	16.1	ns
		$V_{CC} = 1.4 \text{ V} \text{ to } 1.6 \text{ V}$	1.9	4.8	8.5	1.5	9.1	10.1	ns
		$V_{CC} = 1.65 \text{ V} \text{ to } 1.95 \text{ V}$	1.9	3.9	6.6	1.7	7.2	8.0	ns
		V_{CC} = 2.3 V to 2.7 V	1.5	3.1	4.7	1.3	5.4	5.9	ns
		V_{CC} = 3.0 V to 3.6 V	1.4	2.8	4.3	1.3	4.6	5.1	ns

Low-power dual function gate

Symbol	Parameter	Conditions		25 °C		-40	0 °C to +1	25 °C	Unit
			Min	Typ[1]	Max	Min	Max (85 °C)	Max (125 °C) - r 17.9 r 10.8 r 6.0 r 5.3 r 11.4 r 9.1 r 6.7 r 7.3 r 7.3 r 23.7 r	_
C _L = 15 p	ρF								
t _{pd}	propagation delay	A, C to 1Y; see Figure 6	<u>2]</u>						
		$V_{CC} = 0.8 V$	-	24.3	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$	1.3	6.9	13.0	1.2	16.2	17.9	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$	1.7	4.9	8.0	1.4	9.7	10.8	ns
		V_{CC} = 1.65 V to 1.95 V	1.5	4.1	6.4	1.4	7.6	8.4	ns
		V_{CC} = 2.3 V to 2.7 V	1.7	3.4	5.0	1.6	5.4	6.0	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	1.7	3.1	4.4	1.6	4.7	5.3	ns
		A, B to 2Y; see Figure 6	<u>2]</u>						
		$V_{CC} = 0.8 V$	-	28.5	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$	2.1	7.7	16.0	1.9	16.3	18.0	ns
		$V_{CC} = 1.4 \text{ V} \text{ to } 1.6 \text{ V}$	2.2	5.4	9.4	2.4	10.3	11.4	ns
		V_{CC} = 1.65 V to 1.95 V	2.0	4.4	7.4	1.8	8.2	9.1	ns
		V_{CC} = 2.3 V to 2.7 V	1.8	3.6	5.5	1.6	6.0	6.7	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	1.7	3.3	4.8	1.5	5.2	5.8	ns
C _L = 30 p	ρF								
t _{pd}	propagation delay	A, C to 1Y; see Figure 6	2]						
		$V_{CC} = 0.8 V$	-	34.7	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$	2.4	9.2	17.7	2.3	20.9	23.0	ns
		$V_{CC} = 1.4 \text{ V} \text{ to } 1.6 \text{ V}$	2.5	6.5	10.6	2.5	12.2	13.5	ns
		V_{CC} = 1.65 V to 1.95 V	2.5	5.4	8.5	2.4	9.4	10.4	ns
		V_{CC} = 2.3 V to 2.7 V	2.6	4.5	6.4	2.4	7.0	7.7	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	2.5	4.2	5.7	2.3	6.6	7.3	ns
		A, B to 2Y; see Figure 6	2]						
		$V_{CC} = 0.8 V$	-	38.9	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$	2.6	10.0	20.5	2.6	21.5	23.7	ns
		$V_{CC} = 1.4 \text{ V}$ to 1.6 V	2.6	6.9	11.9	2.6	13.2	14.5	ns
		V_{CC} = 1.65 V to 1.95 V	2.7	5.7	9.5	2.7	10.5	11.6	ns
		V_{CC} = 2.3 V to 2.7 V	2.5	4.7	6.9	2.5	7.6	8.4	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	2.4	4.4	6.1	2.4	7.1	7.9	ns

Table 8. Dynamic characteristics ... continued

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Symbol	Parameter	Conditions	25 °C			–40 °C to +125 °C			Unit
			Min	Typ <mark>[1]</mark>	Мах	Min	Max (85 °C)	Max (125 °C)	
C _L = 5 pl	F, 10 pF, 15 pF and	30 pF							
C _{PD}	power dissipation capacitance	$f_i = 1 \text{ MHz}; V_1 = \text{GND to } V_{\text{CC}}$ [3][4]							
		$V_{CC} = 0.8 V$	-	2.7	-	-	-	-	pF
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$	-	2.9	-	-	-	-	pF
		$V_{CC} = 1.4 \text{ V} \text{ to } 1.6 \text{ V}$	-	3.0	-	-	-	-	pF
		$V_{CC} = 1.65 \text{ V} \text{ to } 1.95 \text{ V}$	-	3.1	-	-	-	-	pF
		V_{CC} = 2.3 V to 2.7 V	-	3.5	-	-	-	-	pF
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	-	4.1	-	-	-	-	pF

Table 8. Dynamic characteristics ... continued

[1] All typical values are measured at nominal V_{CC} .

[2] t_{pd} is the same as t_{PLH} and t_{PHL} .

[3] All specified values are the average typical values over all stated loads.

[4] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

 $P_{D} = C_{PD} \times V_{CC}^{2} \times f_{i} \times N + \Sigma (C_{L} \times V_{CC}^{2} \times f_{o}) \text{ where:}$

 f_i = input frequency in MHz;

 f_0 = output frequency in MHz;

 C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

12. Waveforms

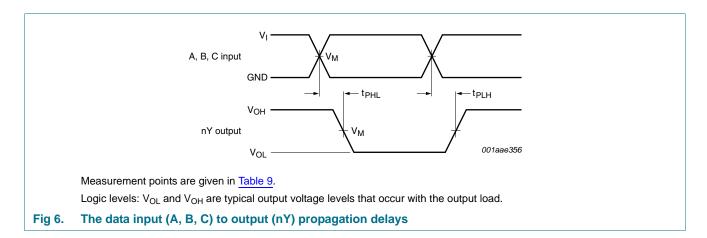


Table 9. **Measurement points**

Supply voltage	Output	Input			
V _{CC}	V _M	V _M	VI	$t_r = t_f$	
0.8 V to 3.6 V	$0.5 imes V_{CC}$	$0.5 imes V_{CC}$	V _{CC}	≤ 3.0 ns	

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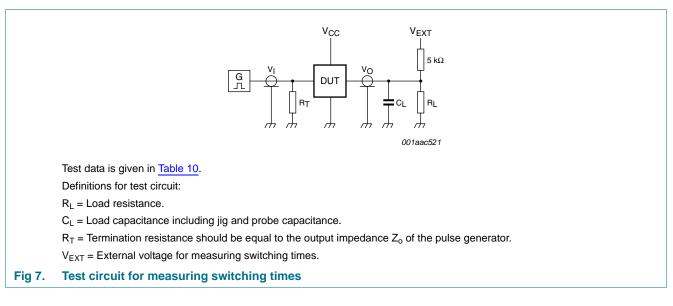


Table 10. Test data

Supply voltage	Load	V _{EXT}			
V _{cc}	CL	R _L [1]	t _{PLH} , t _{PHL}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ}
0.8 V to 3.6 V	5 pF, 10 pF, 15 pF and 30 pF	5 k Ω or 1 M Ω	open	GND	$2 \times V_{CC}$

[1] For measuring enable and disable times $R_L = 5 k\Omega$.

For measuring propagation delays, set-up and hold times and pulse width R_L = 1 M Ω .

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13. Package outline

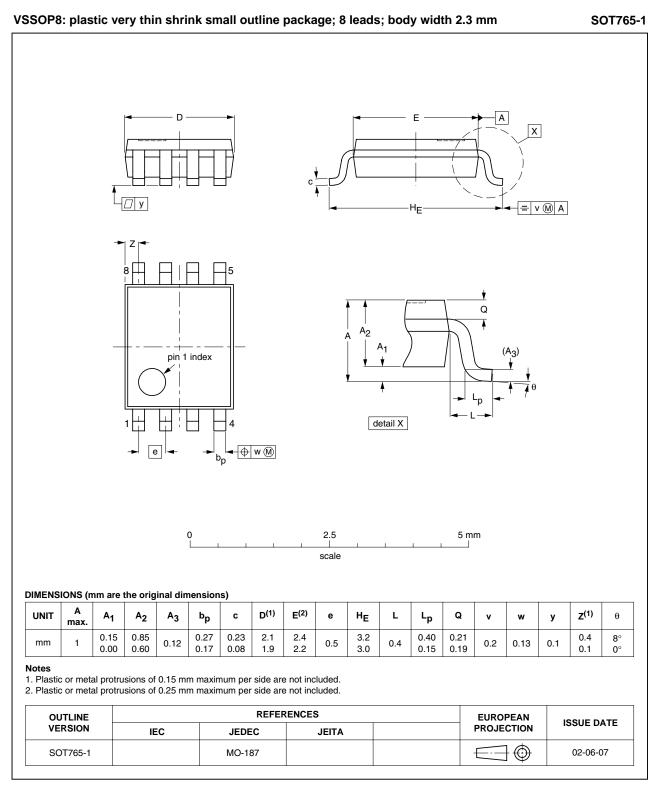
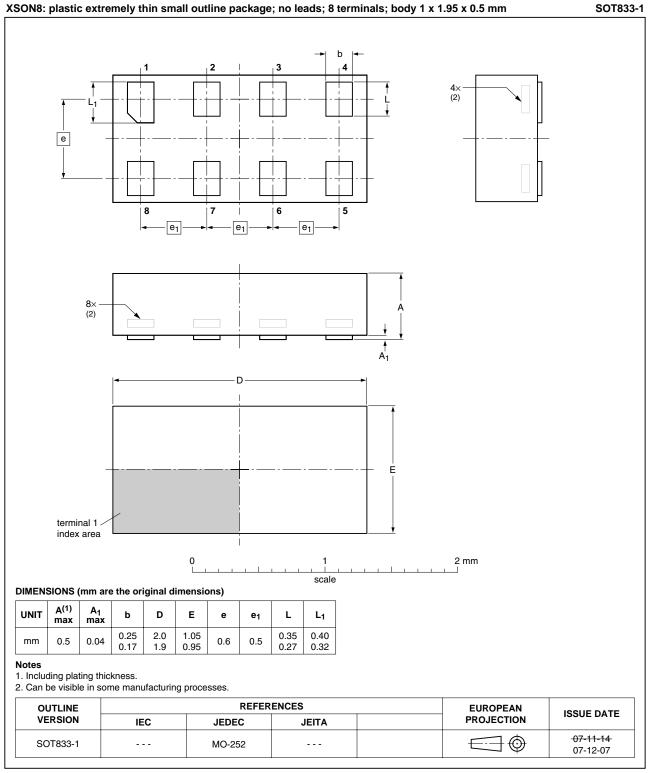


Fig 8. Package outline SOT765-1 (VSSOP8)

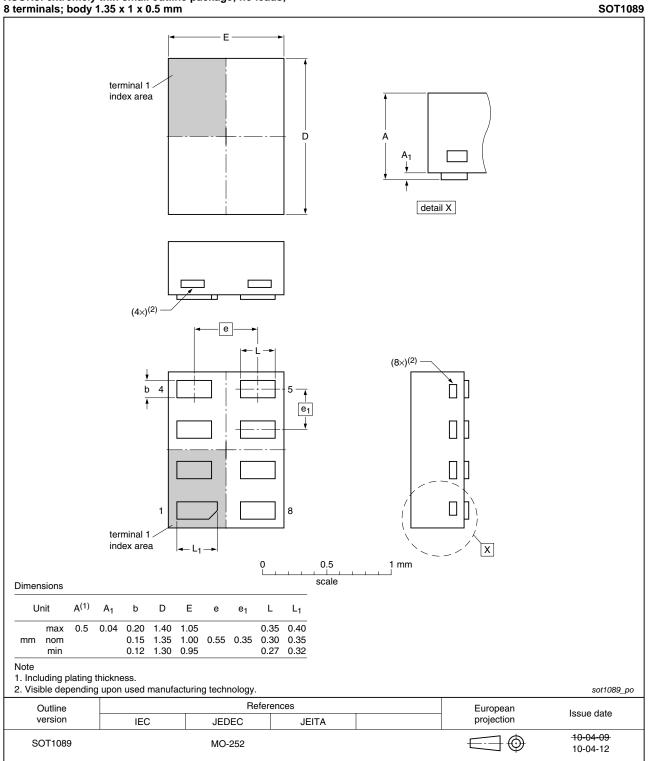
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Package outline SOT833-1 (XSON8) Fig 9.

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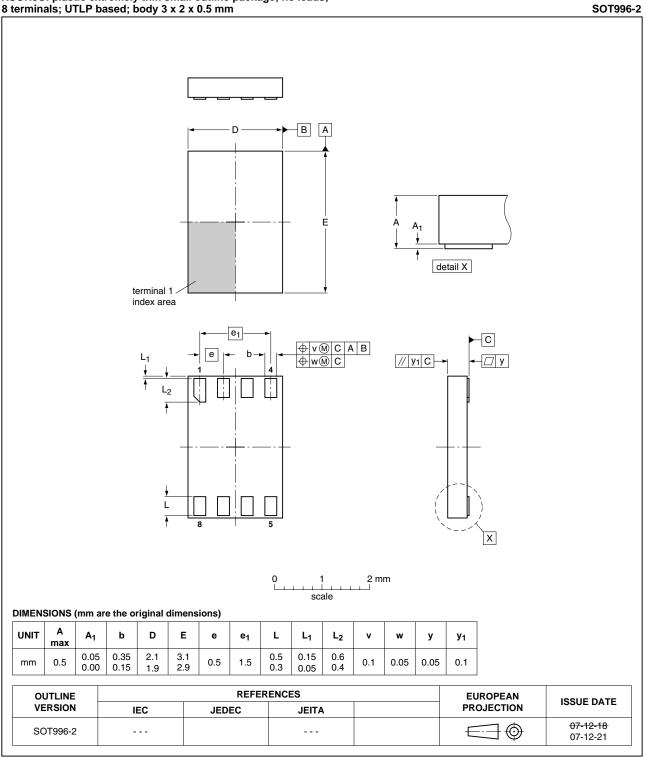


XSON8: extremely thin small outline package; no leads; 8 terminals; body 1.35 x 1 x 0.5 mm

Fig 10. Package outline SOT1089 (XSON8)

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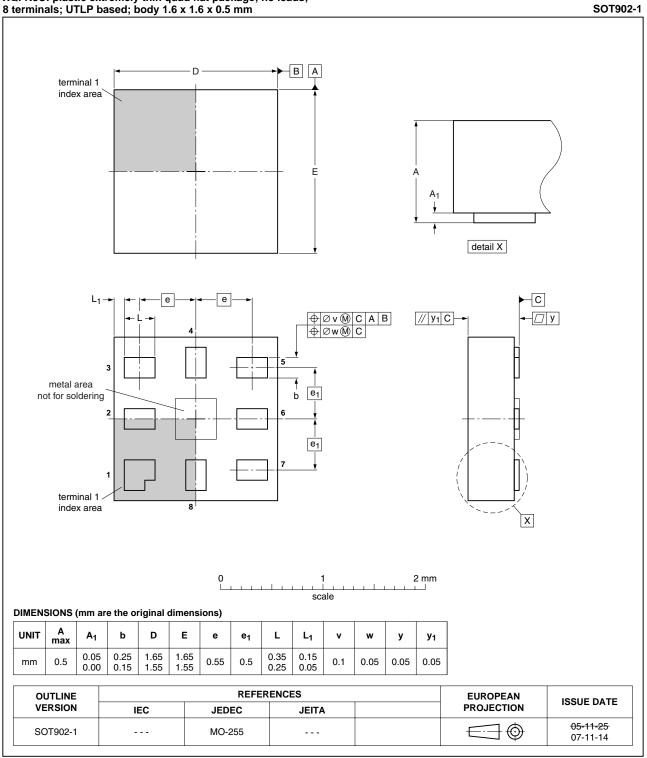


XSON8U: plastic extremely thin small outline package; no leads; 8 terminals; UTLP based; body 3 x 2 x 0.5 mm

Fig 11. Package outline SOT996-2 (XSON8U)

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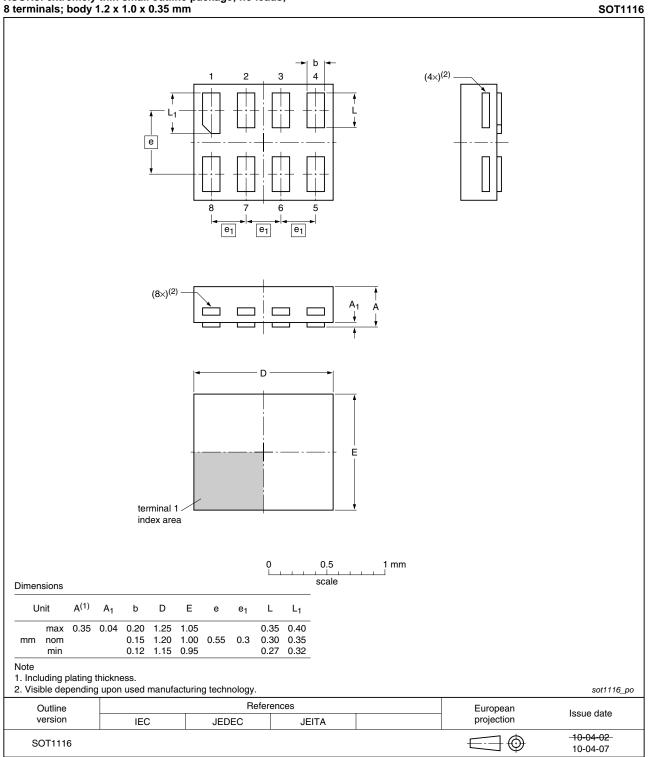




XQFN8U: plastic extremely thin quad flat package; no leads; 8 terminals; UTLP based; body 1.6 x 1.6 x 0.5 mm

Fig 12. Package outline SOT902-1 (XQFN8U)

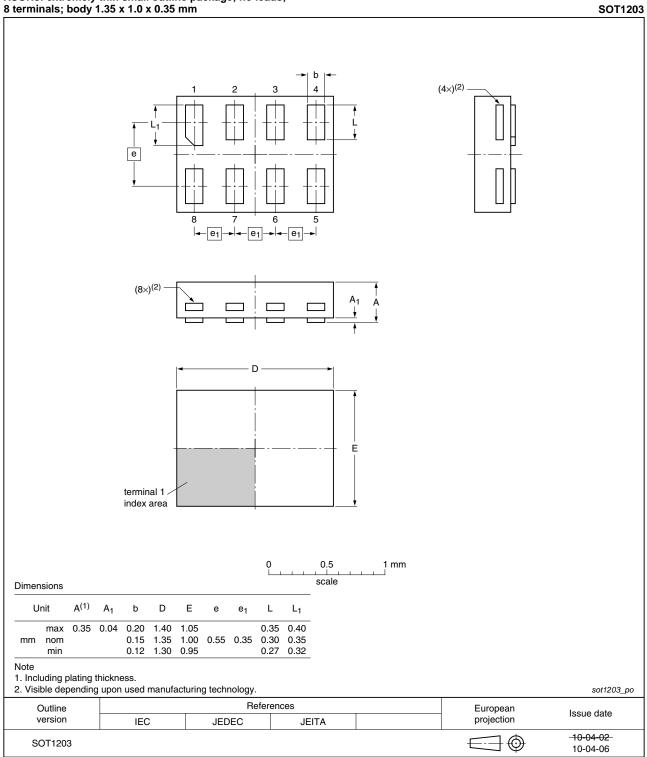
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XSON8: extremely thin small outline package; no leads; 8 terminals; body 1.2 x 1.0 x 0.35 mm

Fig 13. Package outline SOT1116 (XSON8)

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XSON8: extremely thin small outline package; no leads; 8 terminals; body 1.35 x 1.0 x 0.35 mm

Fig 14. Package outline SOT1203 (XSON8)

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14. Abbreviations

Acronym	Description	
CDM	Charged Device Model	
DUT	Device Under Test	
ESD	ElectroStatic Discharge	
НВМ	Human Body Model	
MM	Machine Model	

15. Revision history

Table 12. Revision his	story			
Document ID	Release date	Data sheet status	Change notice	Supersedes
74AUP1G885 v.6	20101021	Product data sheet	-	74AUP1G885 v.5
Modifications:	 Added type r 	number 74AUP1G885GF (SOT	T1089/XSON8 packag	e).
	 Added type r 	number 74AUP1G885GN (SO	T1116/XSON8 packag	e).
	 Added type r 	number 74AUP1G885GS (SO	T1203/XSON8 packag	e).
74AUP1G885 v.5	20090626	Product data sheet	-	74AUP1G885 v.4
74AUP1G885 v.4	20090401	Product data sheet	-	74AUP1G885 v.3
74AUP1G885 v.3	20080328	Product data sheet	-	74AUP1G885 v.2
74AUP1G885 v.2	20070710	Product data sheet	-	74AUP1G885 v.1
74AUP1G885 v.1	20061201	Product data sheet	-	-

16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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